

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

MCH6321 — General-Purpose Switching Device Applications

Features

- 1.8V drive
- · Protection diode in

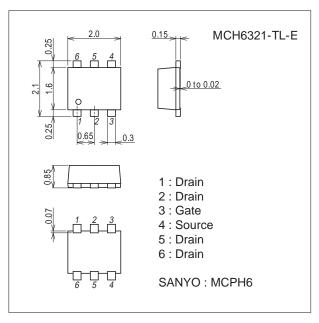
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		-4	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-16	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm ² ×0.8mm)	1.5	W
Channel Temperature	Tch		150	C
Storage Temperature	Tstg		-55 to +150	C

Package Dimensions

unit : mm (typ) 7022A-009



Product & Package Information

• Package : MCPH6

• JEITA, JEDEC : SC-88, SC-70-6, SOT-363

• Minimum Packing Quantity : 3,000 pcs./reel

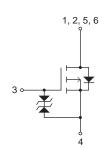
Packing Type: TL

TL

Marking



Electrical Connection

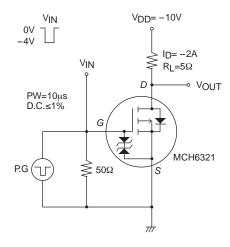


MCH6321

Electrical Characteristics at Ta=25°C

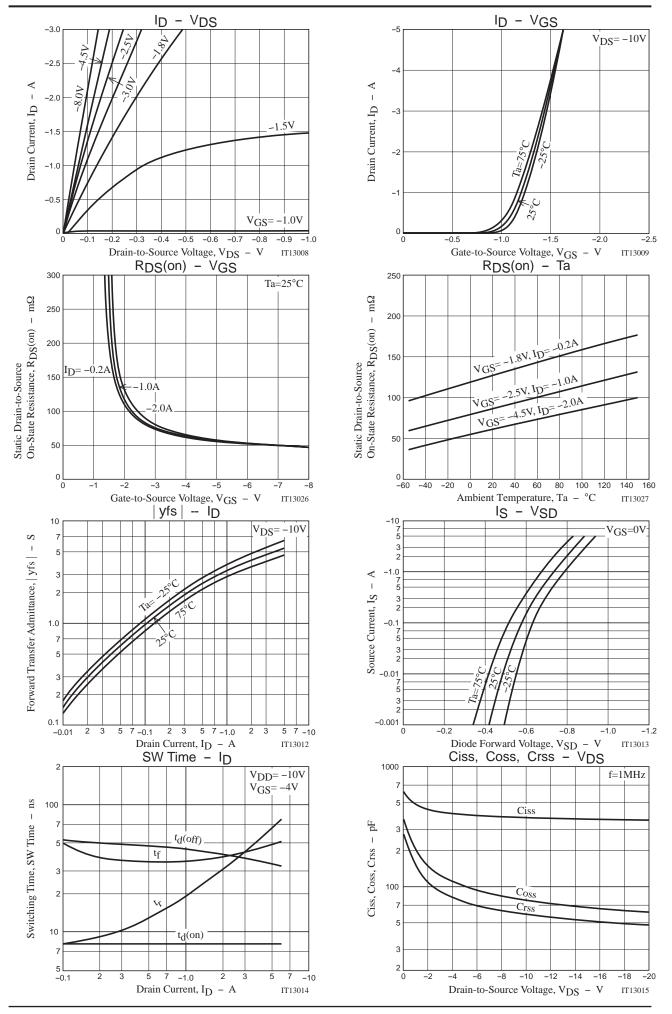
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-20			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-20V, V _{GS} =0V			-1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =-10V, I _D =-1mA	-0.4		-1.3	V	
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-2A	2.5	4.3		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =-2A, V _G S=-4.5V			83	$m\Omega$	
	R _{DS} (on)2	I _D =-1A, V _G S=-2.5V		88	125	$m\Omega$	
	R _{DS} (on)3	I _D =-0.2A, V _G S=-1.8V		130	200	mΩ	
Input Capacitance	Ciss			375		pF	
Output Capacitance	Coss	V _{DS} =-10V, f=1MHz		77		pF	
Reverse Transfer Capacitance	Crss			58		pF	
Turn-ON Delay Time	t _d (on)			8.1		ns	
Rise Time	t _r	Con an acified Test Circuit	31			ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		40		ns	
Fall Time	tf			39		ns	
Total Gate Charge	Qg			4.6		nC	
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-4A		0.8		nC	
Gate-to-Drain "Miller" Charge	Qgd]		1.3		nC	
Diode Forward Voltage	V _{SD}	I _S =-4A, V _G S=0V		-0.86	-1.2	V	

Switching Time Test Circuit

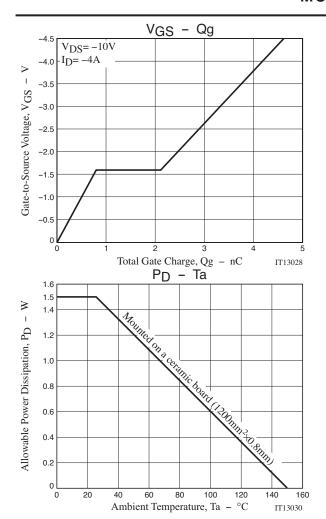


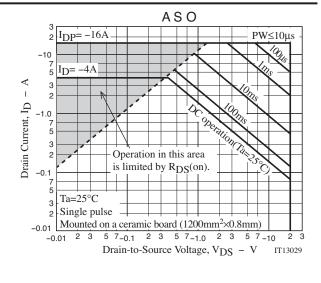
Ordering Information

Device	Package	Shipping	memo	
MCH6321-TL-E	CH6321-TL-E MCPH6		Pb Free	



MCH6321



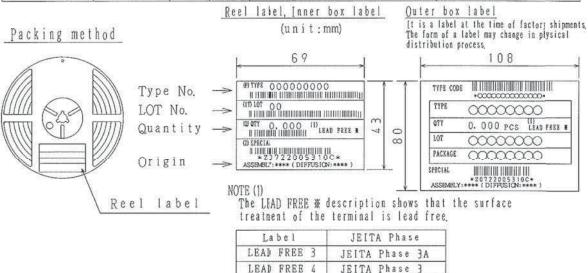


Taping Specification

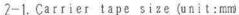
MCH6321-TL-E

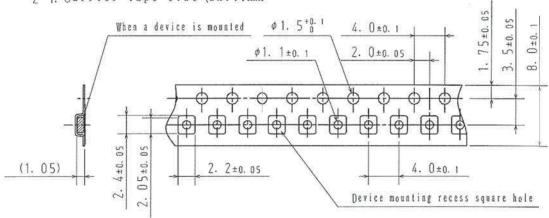
1. Packing Format

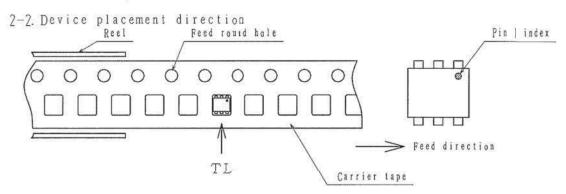
Package Name Carrier Tape Type	Carrier Tape	arrier Tape Maxi		r of ed (yes)	Packing format		
	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)		
МСРН6	MCP4	3, 000	15, 000	90, 000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210	



2. Taping configuration





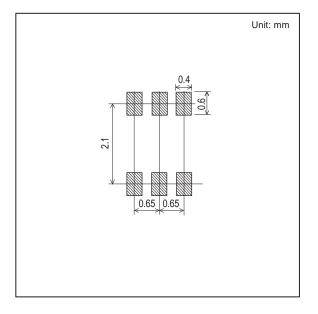


Those with pin 1 index on the feed hole side ·····TL

Outline Drawing

MCH6321-TL-E

Land Pattern Example



Note on usage: Since the MCH6321 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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